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	FORMATION DISCLOSURE TATEMENT BY APPLICANT				First Named Inventor	Theodore W. Houston	
					Group Art Unit	2811	
	(use as many sheets as necessary)				Examiner Name	Douglas W. Owens	
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US and Foreign Patent Documents: ¹Unique citation designation number. ²See attached Kinds of U.S. Patent Documents. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. Skind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. Applicant is to place a check mark here if English language Translation is attached.

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